

METHOD OF PREVENTING RESIST POISONING IN DUAL DAMASCENE STRUCTURES

Abstract of the Disclosure

5 A method for forming a dual damascene interconnect in a dielectric layer is
provided. Generally, a first aperture is etched in the dielectric. A poison barrier layer
is formed over part of the dielectric, which prevents resist poisoning. A patterned
mask is formed over the poison barrier layer. A second aperture is etched into the
dielectric layer, wherein at least part of the first aperture shares the same area as at
10 least part of the second aperture.